

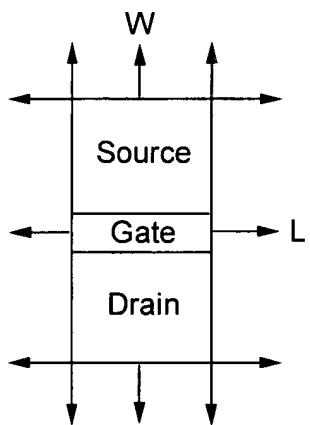


F1S920030235US1 (TLT)
Haining, S. Yang, et al.

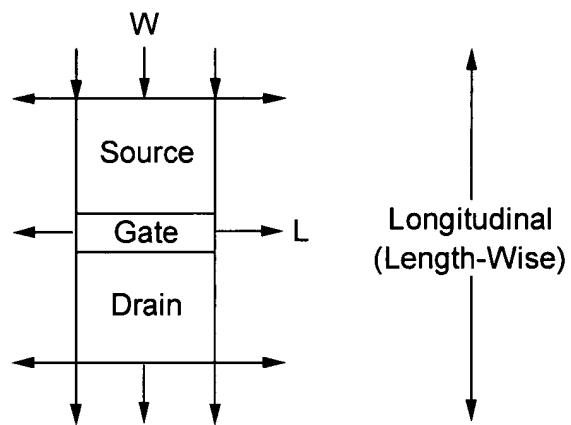
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FIG. 1

NFET



PFET



Transverse
(Width-Wise)

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FIG. 2A

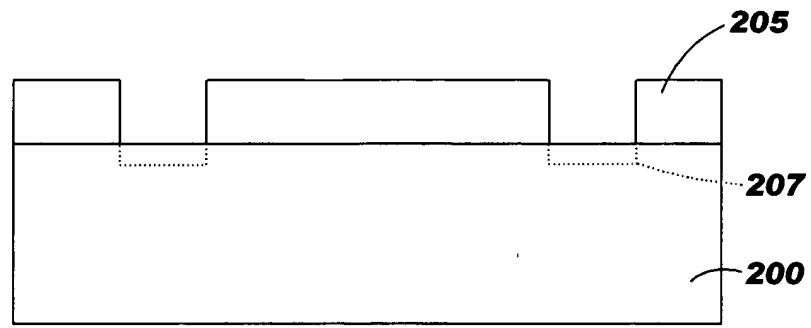


FIG. 2B

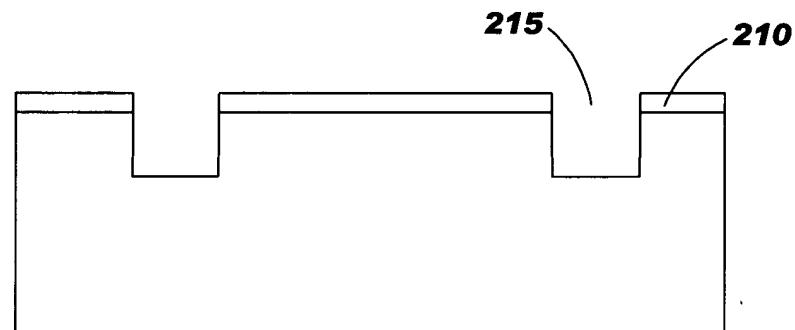
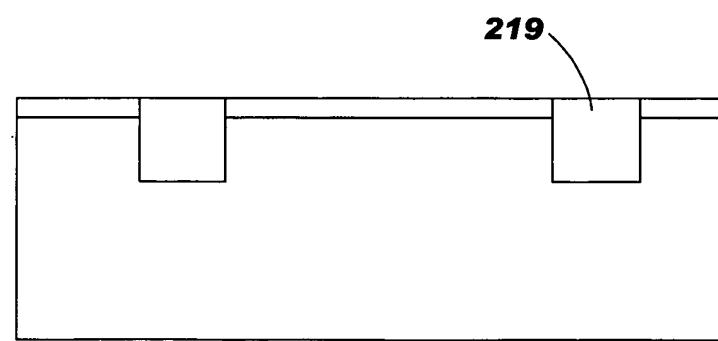


FIG. 2C



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FIG. 2D

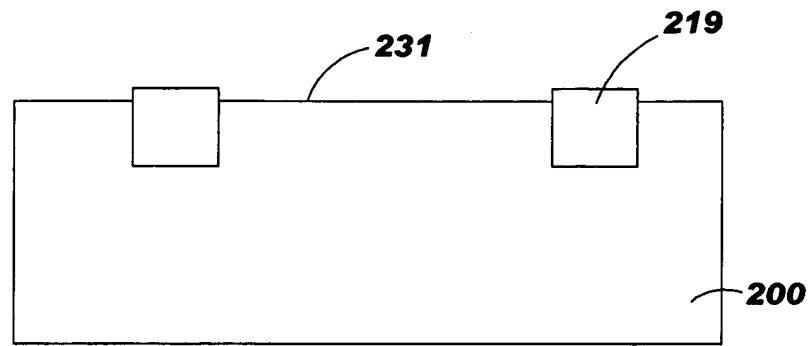


FIG. 2E

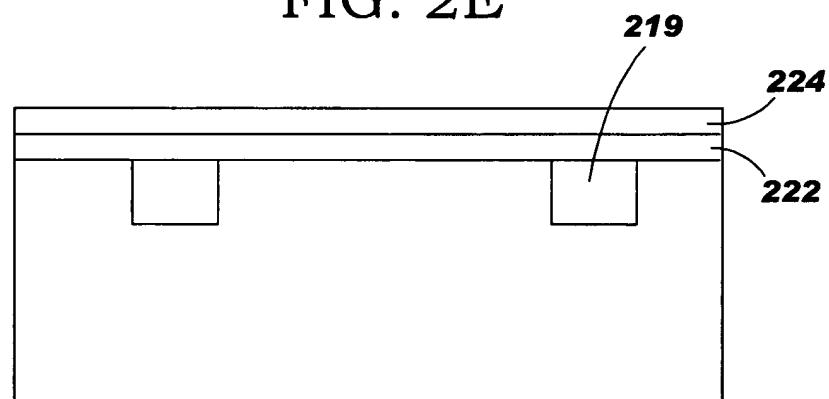
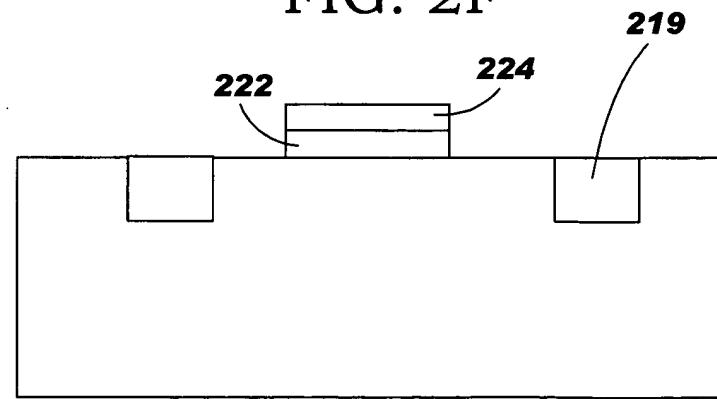


FIG. 2F



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FIG. 2G

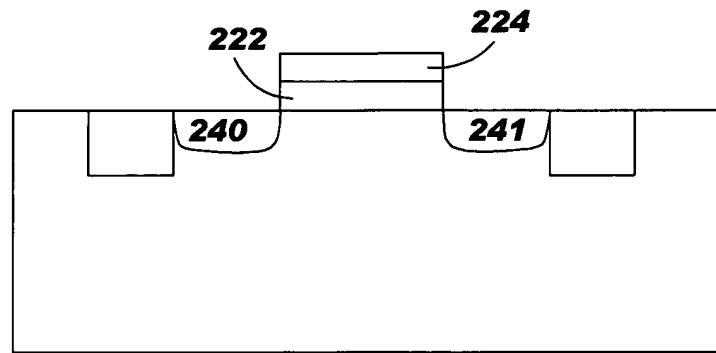


FIG. 2H

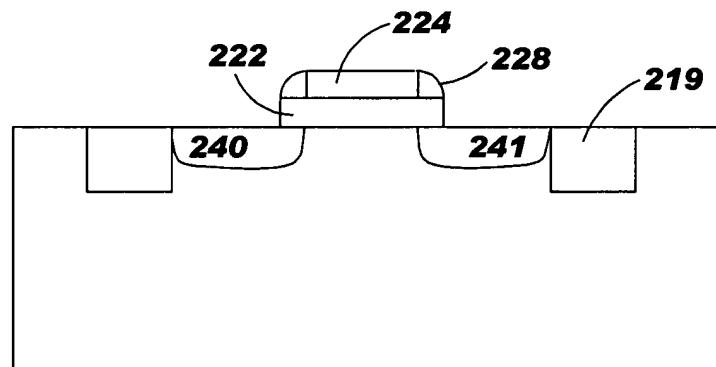
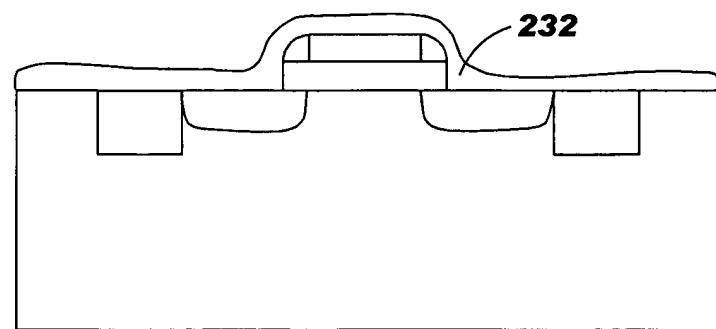


FIG. 2I



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FIG. 2J

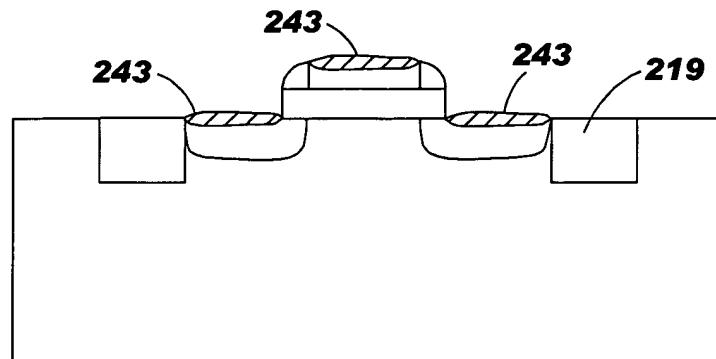


FIG. 2K

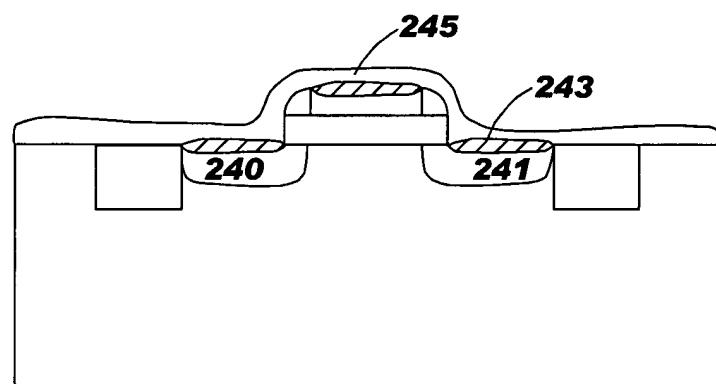
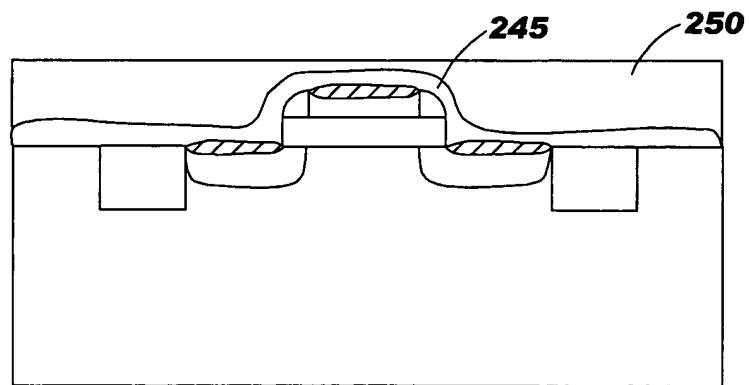


FIG. 2L



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FIG. 3

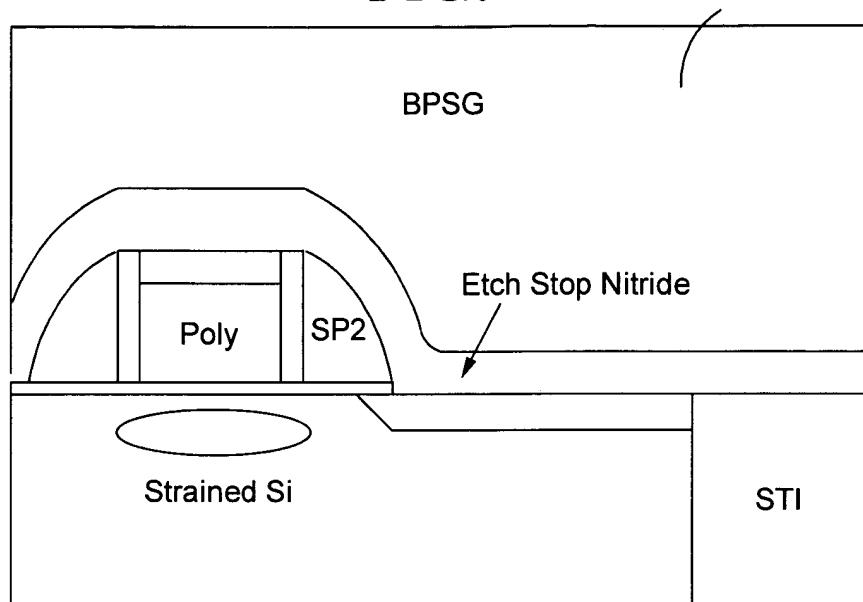
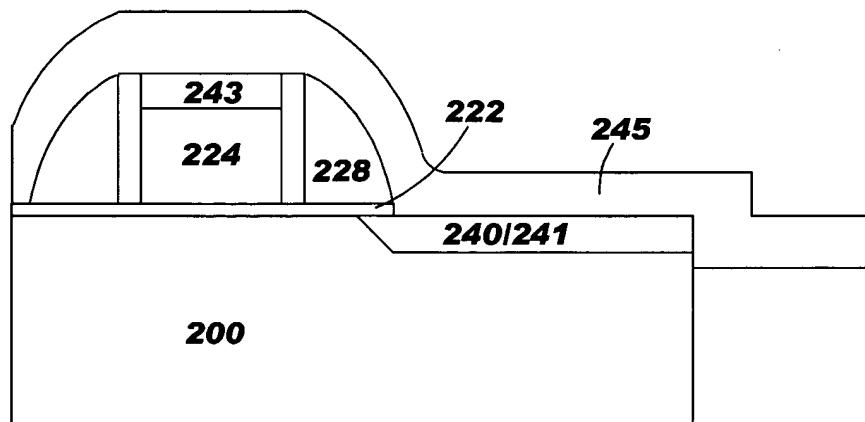


FIG. 4



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FIG. 5

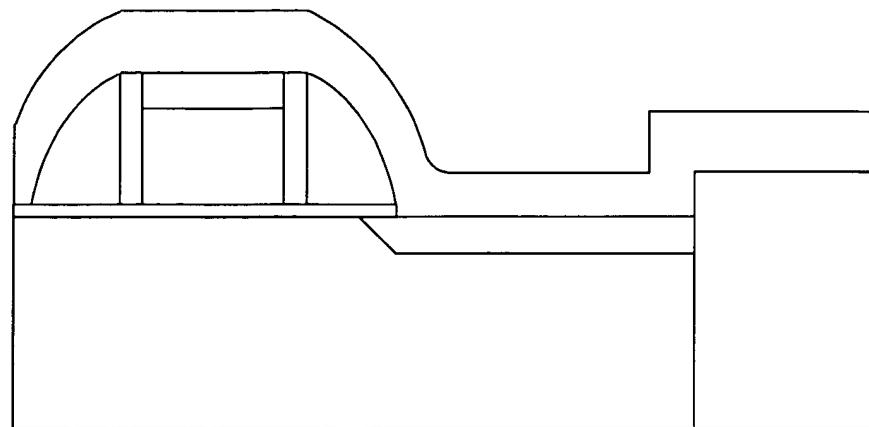
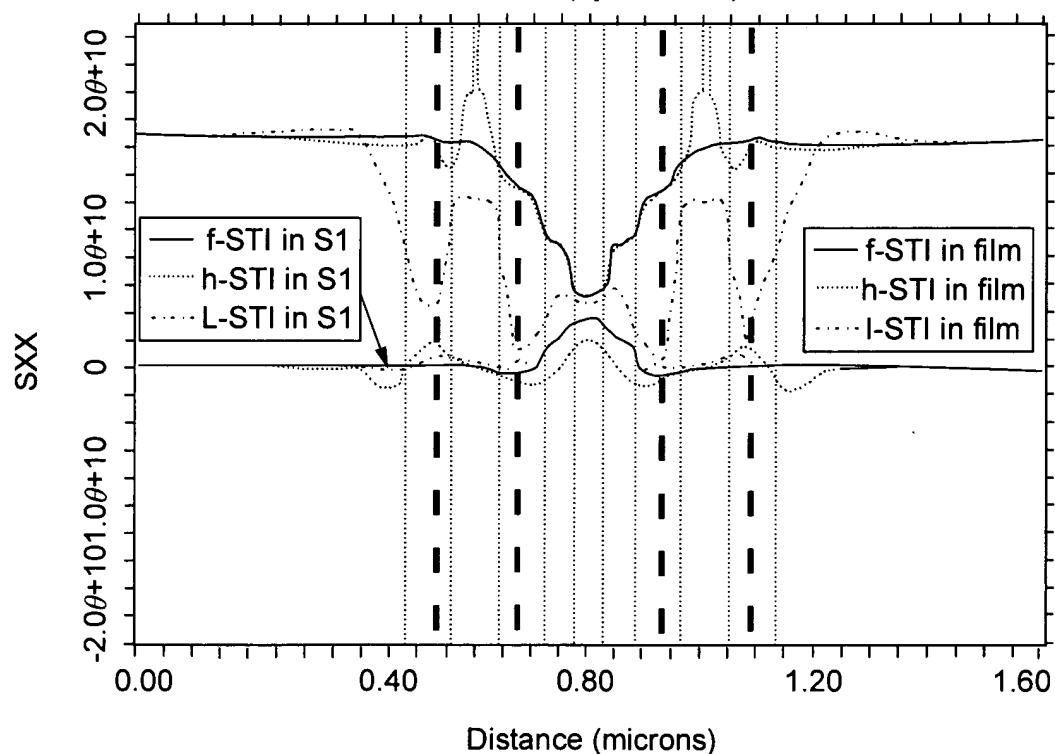
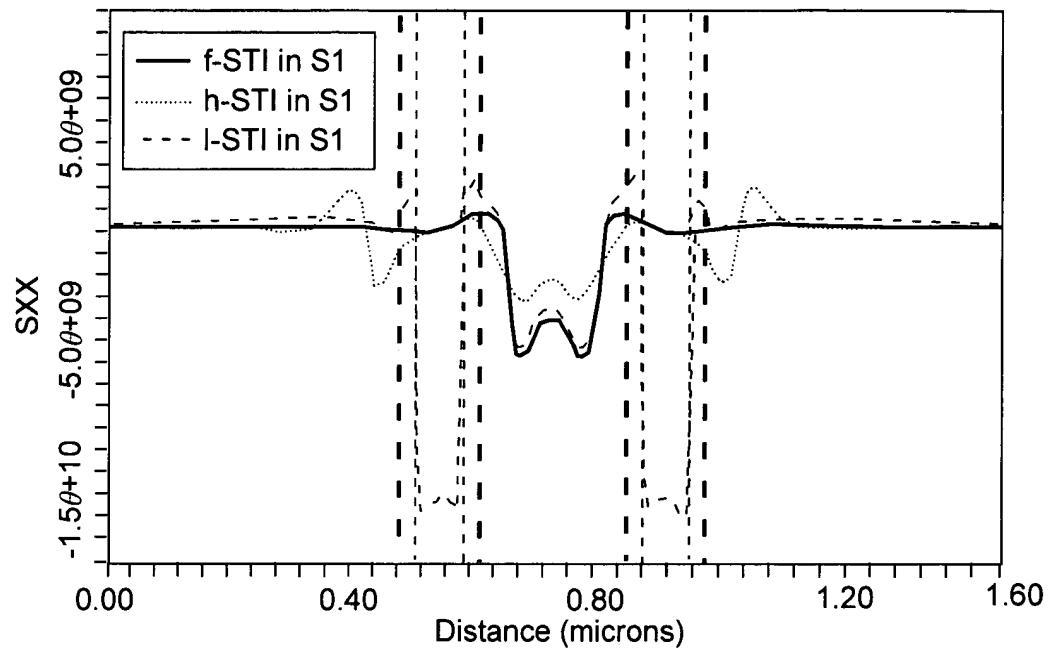


FIG. 6

Stress S_{xx} vs. hight of STI-oxide
In Si cut at $y= +0.01\mu m$ and In film $y= -0.01\mu m$
Pressure (dynes/cm 2)



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 Stress S_{xx} vs. hight of STI-oxide
 in Si cut at $y=+0.01\text{um}$
 Pressure (dynes/cm²)



Stress S_{xx} vs. hight of STI-oxide w/large PC-STI distance
 in Si cut at $y=0.01\text{um}$ and in film $y=0.01\text{um}$

FIG. 7

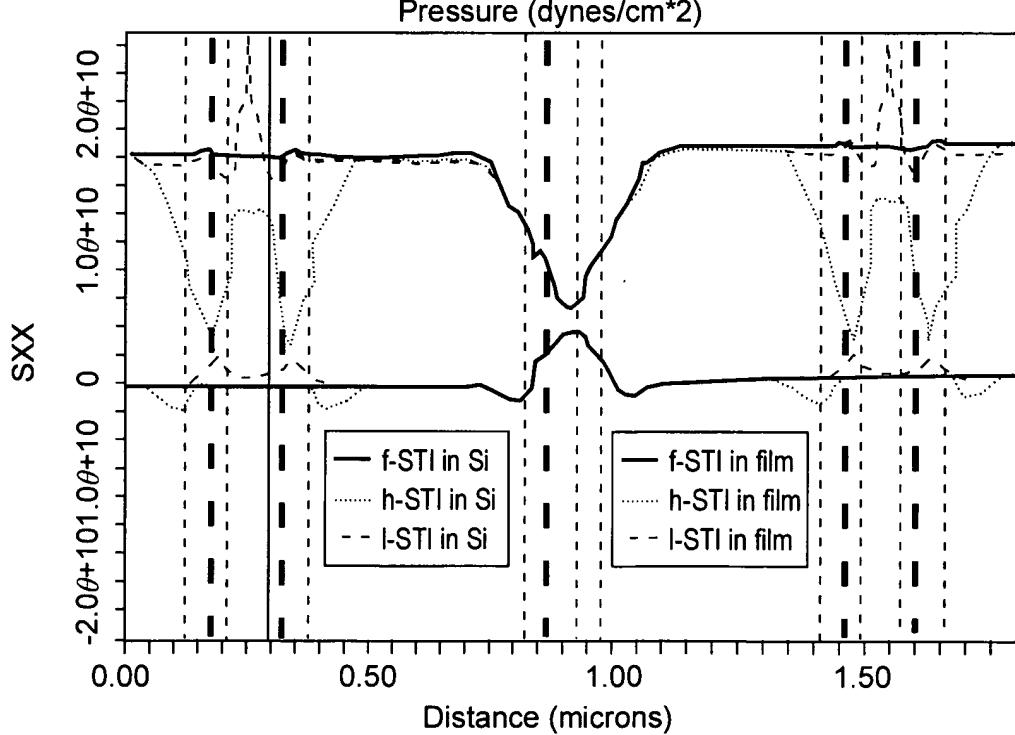


FIG. 8